



DOCUMENT CHANGE REQUEST

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|------------|-------------|-----------------------|------------|---------------|--------------------|
| DCR number | 1026 | Changes required for: | General | Originator: | André Uguen |
| Date: | 2016/12/06 | Date sent: | 2016/08/04 | Organisation: | STMicroelectronics |
| Status: | IMPLEMENTED | | | | |

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| Title: | Integrated Circuits, Silicon Monolithic, Pulse Width Modulator based on Type ST1843 |
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| Number: | 9108/020 | Issue: | 3 |
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Other documents affected:

9108/021-2

Page:

page 13

Paragraph:

2.3.2 High and Low temperature measurement

Original wording:


Line regulation V_{REF_LINE} 12V V_i 25V; $RT = 10K$; $CT=3.3nF$ with limit: 0.05 V (for ST1843) or 22mV (for ST1845)

Proposed wording:

Line regulation V_{REF_LINE} 12V V_i 25V; $RT = 10K$; $CT=3.3nF$ 0.22 V for both devices

Justification:

initially we have proposed the following limits for this parameter: 220mV for ST1845 and 50mV for ST1843. in 9108020 it was correct but a typo was introduced in 9108021 transforming 0.22v in 22mV. We would like to take the benefit of this DCR for typo correction in order to align the two devices for this parameter. In fact the actual values at -55°C are the highest, and it depends from one diffusion lot to the other. Aligning the two devices for this parameter will allow to use a new diffusion lot

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| Attachments: |
| N/A |
| Modifications: |
| N/A |
| Approval signature: |
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| Date signed: |
| 2016-12-06 |